ELECTRONICS, INC.
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# NTE267
# Silicon NPN Transistor
# High Gain Darlington Power Amp, Switch

**Features:**
- Forward Current Transfer Ratio: $h_{FE}$ = 90,000 min.
- Free−Air Power Dissipation: 1.33W @ $T_A$ = +50°C
- Hard Solder Mountdown

**Applications:**
- Driver
- Regulator
- Audio Output
- Relay Substitute
- Touch Switch
- Oscillator
- IC Driver
- Servo Amplifier
- Capacitor Multiplier

**Absolute Maximum Ratings:** ($T_A$ = +25°C, unless otherwise specified)

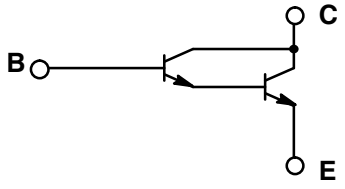
Collector to Emitter, $V_{CEO}$ . . . . . 30V
Emitter to Base, $V_{EBO}$ . . . . . 13V
Collector to Emitter, $V_{CES}$ . . . . . 30V
Collector Current, $I_C$
  Continuous . . . . . 500mA
  Peak . . . . . 1A
Power Dissipation, $P_T$
  Tab at +25°C . . . . . 6.25W
  Free Air at +50°C $^w$/Tab . . . . . 1.33W
Thermal Resistance, Junction to Case (Note 1), $R_{thJC}$ . . . . . 20°C/W
Thermal Resistance, Junction to Ambient (Note 1), $R_{thJA}$ . . . . . 75°C/W
Operating Junction Temperature Range, $T_J$ . . . . . −55° to +150°C
Storage Temperature Range, $T_{stg}$ . . . . . −55° to +150°C
Lead Temperature (During Soldering, 1/16” ±1/32” from case, 10sec max), $T_L$ . . . . . +260°C

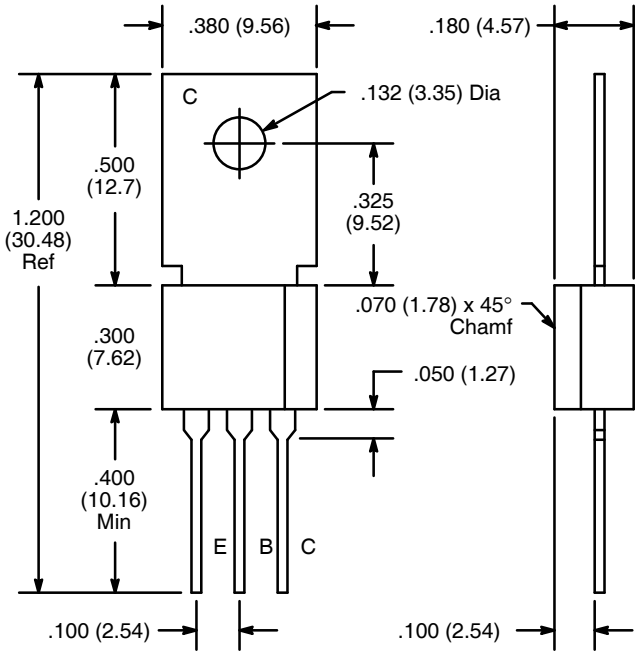
Note 1. Tab temperature is measured on center of tab, 1/16” from plastic body.

**Electrical Characteristics:** ($T_A$ = +25°C, unless otherwise specified)

| Parameter | Symbol | Test Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| Forward Current Transfer Ratio | $h_{FE}$ | $V_{CE}$ = 5V, f = 1kHz | $I_C$ = 200mA | 90k | – | – | |
| | | | $I_C$ = 20mA | 90k | – | – | |
| Collector Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C$ = 500mA, $I_B$ = 0.5mA, Note 2 | | – | – | 1.5 | V |
| Base Emitter Saturation Voltage | $V_{BE(sat)}$ | $I_C$ = 500mA, $I_B$ = 0.5mA | | – | – | 2.0 | V |
| Collector Cutoff Current | $I_{CES}$ | $V_{CE}$ = Rated $V_{CES}$, $T_J$ = +25°C | | – | – | 0.5 | µA |
| | $I_{CBO}$ | $V_{CE}$ = Rated $V_{CES}$, $T_J$ = +150°C | | – | – | 20 | µA |
| Emitter Cutoff Current | $I_{EBO}$ | $V_{EB}$ = 13V | | – | – | 0.1 | µA |
| Collector Capacitance | $C_{cbo}$ | $V_{CB}$ = 10V, f = 1MHz | | – | 5 | 10 | pF |
| Gain Bandwidth Product | $f_T$ | $V_{CE}$ = 5V, $I_C$ = 20mA | | – | 75 | – | MHz |
| **Switching Times** | | | | | | | |
| Delay Time and Rise Time | $t_d$ & $t_r$ | $I_C$ = 1A, $I_{B1}$ = 1mA | | – | 100 | – | ns |
| Storage Time | $t_s$ | $I_C$ = 1A, $I_{B1}$ = $I_{B2}$ = 1mA | | – | 350 | – | ns |
| Fall Time | $t_f$ | $I_C$ = 1A, $I_{B1}$ = $I_{B2}$ = 1mA | | – | 800 | – | ns |

Note 2. Pulsed measurement, 300µsec pulse width, duty cycle ≤ 2%.



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